



MMBT3904FN3

NPN GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts **POWER** 250 mWatts

DFN 3L Unit : inch(mm)

FEATURES

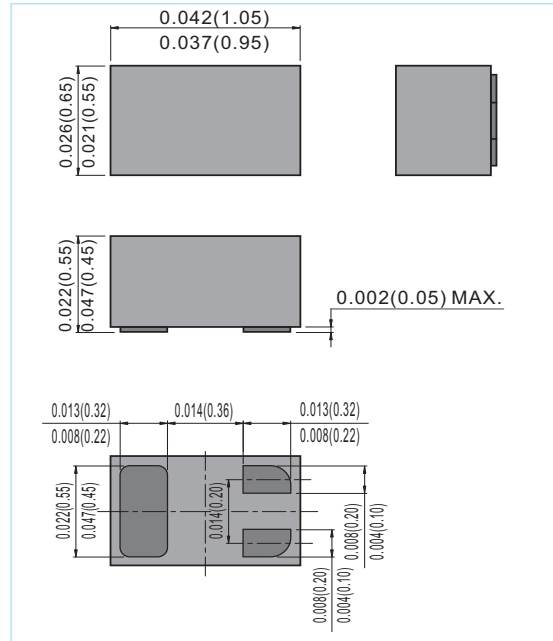
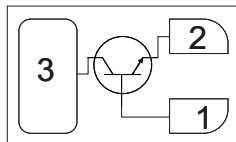
- NPN epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 40V$
- Collector current $I_C = 200mA$
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

Case: DFN 3L, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Marking: AC



ABSOLUTE RATINGS

Parameter	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	40	V
Collector - Base Voltage	V_{CBO}	60	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	200	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	250	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	500	$^{\circ}C/W$
Junction Temperature	T_J	-55 to +150	$^{\circ}C$
Operating Temperature	T_{STG}	-55 to +150	$^{\circ}C$

Note 1: Transistor mounted on FR-4 board 70 x 60 x 1mm.

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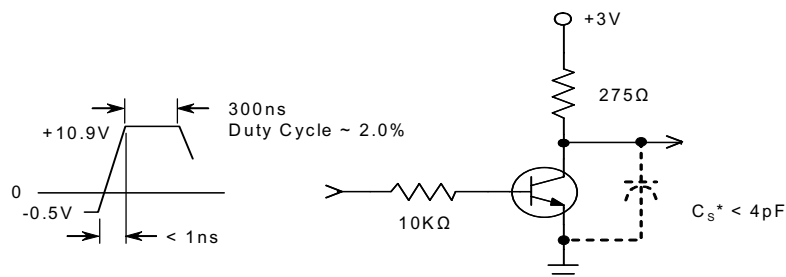
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ELECTRICAL CHARACTERISTICS

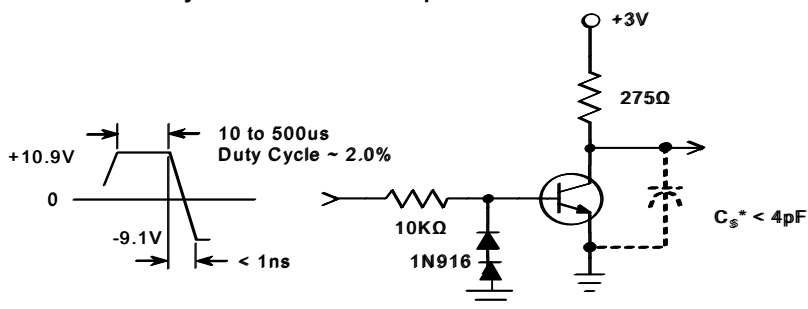
Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1.0mA, I_B=0$	40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6.0	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE}=30V, V_{EB}=3.0V$	-	-	50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=30V, V_{EB}=3.0V$	-	-	50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C=0.1mA, V_{CE}=1.0V$	40	-	-	-
		$I_C=1.0mA, V_{CE}=1.0V$	70	-	-	
		$I_C=10mA, V_{CE}=1.0V$	100	-	300	
		$I_C=50mA, V_{CE}=1.0V$	60	-	-	
		$I_C=100mA, V_{CE}=1.0V$	30	-	-	
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=50mA, I_B=5.0mA$	-	-	0.2 0.3	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=50mA, I_B=5.0mA$	0.65 -	- -	0.85 0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB}=5V, I_E=0, f=1MHz$	-	-	4.0	pF
Emitter - Base Capacitance	C_{EBO}	$V_{EB}=0.5V, I_C=0, f=1MHz$	-	-	8.0	pF
Delay Time	t_d	$V_{CC}=3V, V_{BE}=-0.5V, I_C=10mA, I_B=1.0mA$	-	-	35	ns
Rise Time	t_r	$V_{CC}=3V, V_{BE}=-0.5V, I_C=10mA, I_B=1.0mA$	-	-	35	ns
Storage Time	t_s	$V_{CC}=3V, I_C=10mA, I_B1=I_B2=1.0mA$	-	-	200	ns
Fall Time	t_f	$V_{CC}=3V, I_C=10mA, I_B1=I_B2=1.0mA$	-	-	50	ns

Note 2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Delay and Rise Time Equivalent Test Circuit



Storage and Fall Time Equivalent Test Circuit



ELECTRICAL CHARACTERISTICS CURVE

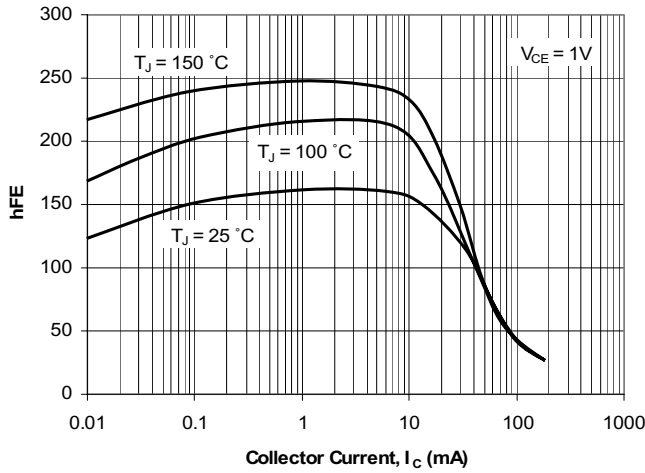


Fig. 1. Typical h_{FE} vs Collector Current

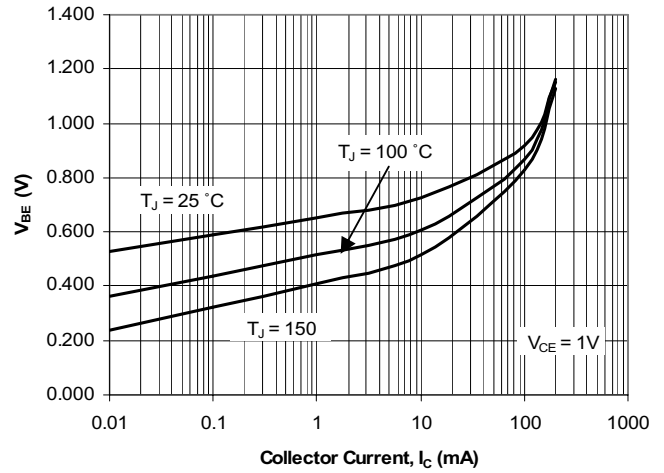


Fig. 2. Typical V_{BE} vs Collector Current

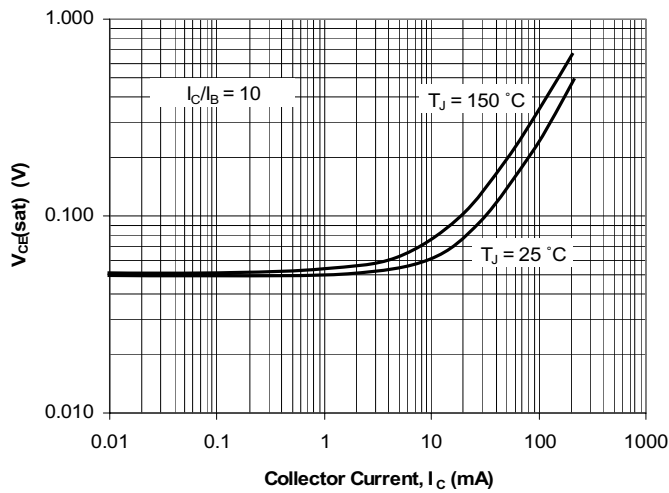


Fig. 3. Typical V_{CE} (sat) vs Collector Current

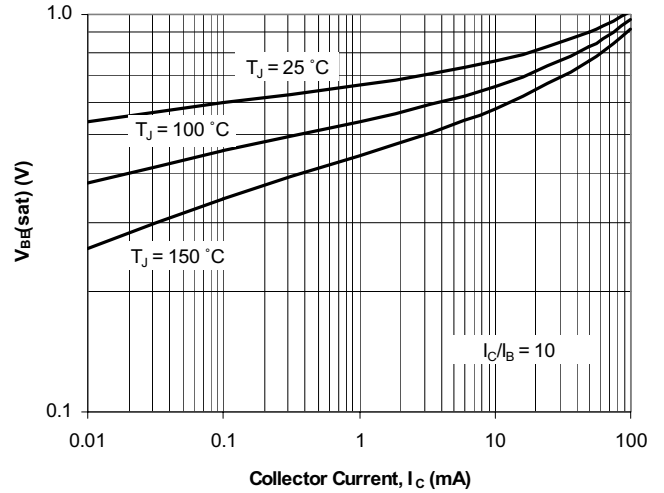


Fig. 4. Typical V_{BE} (sat) vs Collector Current

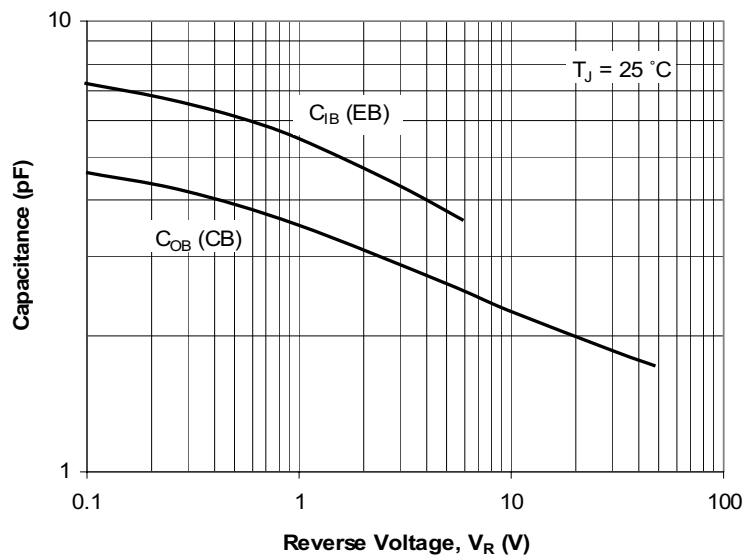
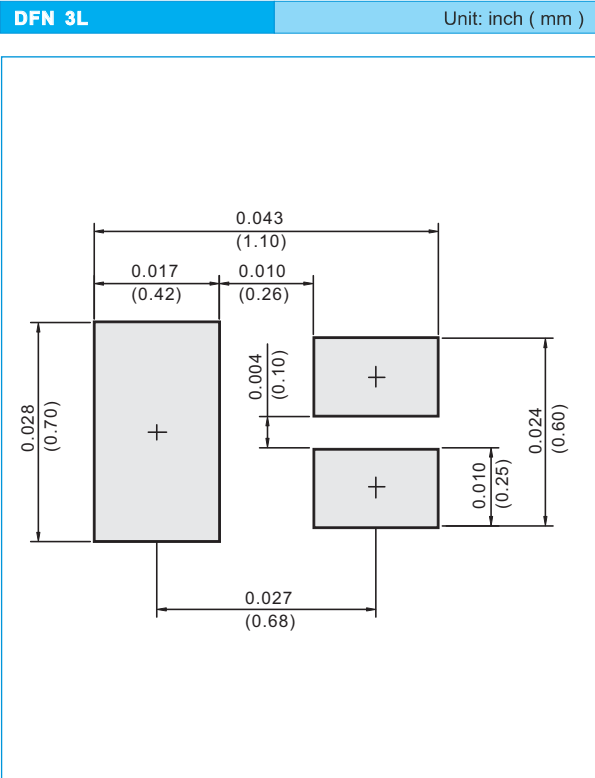


Fig. 5. Typical Capacitances vs Reverse Voltage



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
T/R - 8K per 7" plastic Reel

LEGAL STATEMENT

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